



## Transistors

## ●Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CBO</sub>	15	V
Collector-emitter voltage	V <sub>CEO</sub>	12	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Collector current	I <sub>C</sub>	1.5	A
	I <sub>CP</sub>	3	A *
Power dissipation	P <sub>C</sub>	200	mW
Junction temperature	T <sub>J</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	-40 to +125	°C

\*Single pulse, P<sub>w</sub>=1ms

Di2

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	25	V
Average rectified forward current	I <sub>F</sub>	700	mA
Forward current surge peak (60Hz, 1∞)	I <sub>FSM</sub>	3	A
Reverse voltage (DC)	V <sub>R</sub>	20	V
Junction temperature	T <sub>J</sub>	125	°C
Range of storage temperature	T <sub>stg</sub>	-40 to +125	°C

## ●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	15	-	-	V	I <sub>C</sub> =10μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	12	-	-	V	I <sub>C</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =10μA
Collector cutoff current	I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> =15V
Emitter cutoff current	I <sub>EBO</sub>	-	-	100	nA	V <sub>EB</sub> =6V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	-	85	200	mV	I <sub>C</sub> /I <sub>B</sub> =500mA/25mA
DC current gain	h <sub>FE</sub>	270	-	680	-	V <sub>CE</sub> /I <sub>C</sub> =2V/200mA *
Transition frequency	f <sub>T</sub>	-	400	-	MHz	V <sub>CE</sub> =2V, I <sub>E</sub> =-200mA, f=100MHz *
Collector output capacitance	C <sub>ob</sub>	-	12	-	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz

\*Pulsed

Di2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>	-	-	490	mV	I <sub>F</sub> =700mA
Reverse current	I <sub>R</sub>	-	-	200	μA	V <sub>R</sub> =20V

Transistors

●Electrical characteristic curves

Tr1

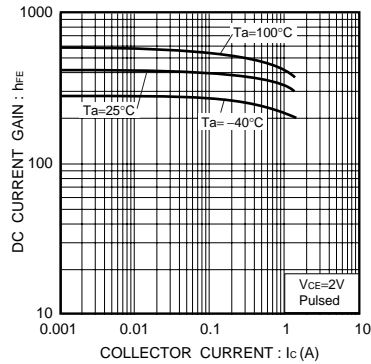


Fig.1 DC current gain vs. collector current

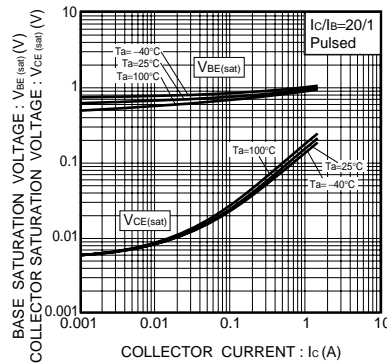


Fig.2 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

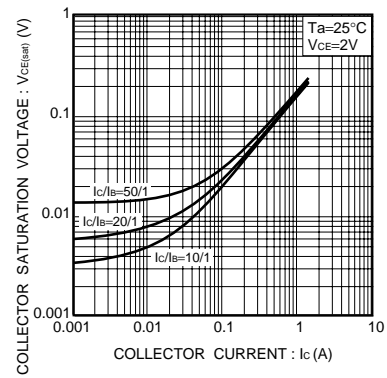


Fig.3 Collector-emitter saturation voltage vs. collector current

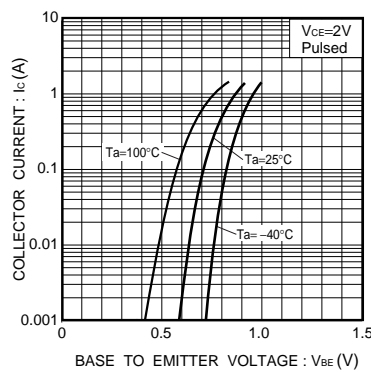


Fig.4 Grounded emitter propagation characteristics

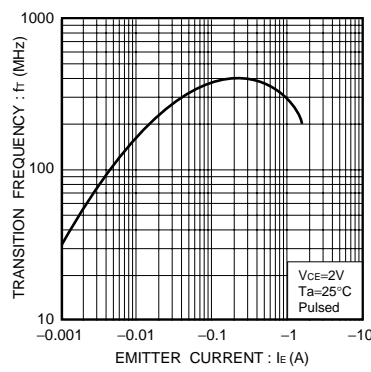


Fig.5 Gain bandwidth product vs. emitter current

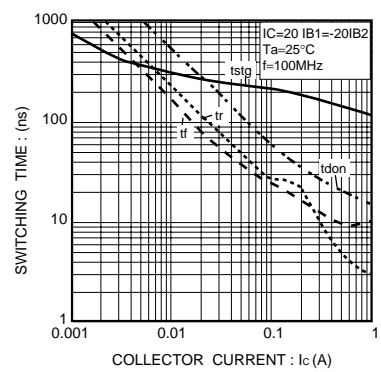


Fig.6 Switching time

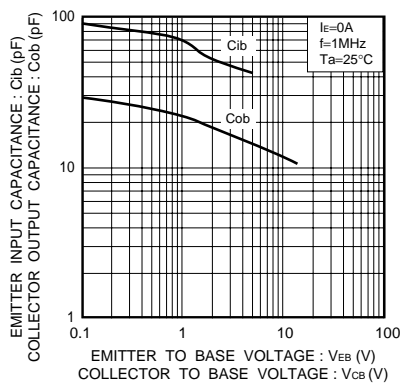


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

Transistors

Di2

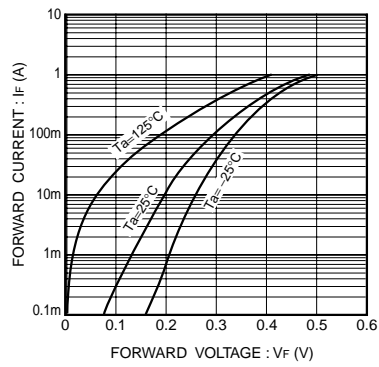


Fig.9 Forward characteristics

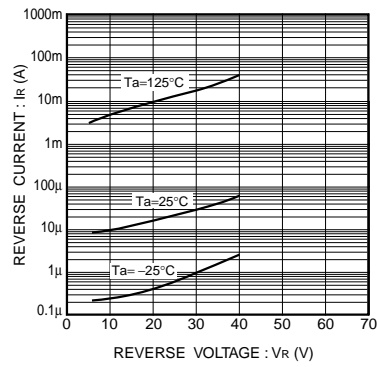


Fig.10 Reverse characteristics

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